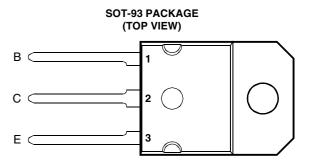
BOURNS®

- Designed for Complementary Use with the TIP2955 Series
- 90 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Collector-base voltage (I _E = 0)	V _{CBO}	100	V
Collector-emitter voltage (I _B = 0) (see Note 1)	V _{CER}	70	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current	I _C	15	Α
Continuous base current	I _B	7	Α
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	P _{tot}	90	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)	P _{tot}	3.5	W
Unclamped inductive load energy (see Note 4)	½LI _C ²	62.5	mJ
Operating junction temperature range	T _j	-65 to +150	°C
Storage temperature range	T _{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds	T _L	260	°C

NOTES: 1. This value applies when the base-emitter resistance R_{BE} = 100 Ω .

- 2. Derate linearly to 150°C case temperature at the rate of 0.72 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = 10 V.



electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 30 mA	I _B = 0	(see Note 5)	60			V
I _{CER}	Collector-emitter cut-off current	V _{CE} = 70 V	$R_{BE} = 100 \Omega$				1	mA
I _{CEO}	Collector cut-off current	V _{CE} = 30 V	I _B = 0				0.7	mA
I _{CEV}	Voltage between base and emitter	V _{CE} = 100 V	V _{BE} = -1.5 V				5	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 7 V	I _C = 0				5	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = 4 V$ $V_{CE} = 4 V$	$I_C = 4A$ $I_C = 10A$	(see Notes 5 and 6)	20 5		70	
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = 0.4 \text{ A}$ $I_B = 3.3 \text{ A}$	$I_C = 4A$ $I_C = 10A$	(see Notes 5 and 6)			1.1 3	V
V _{BE}	Base-emitter voltage	V _{CE} = 4 V	I _C = 4 A	(see Notes 5 and 6)			1.8	V
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	$I_C = 0.5 A$	f = 1 kHz	15			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 0.5 A	f = 1 MHz	3	_		

NOTES: 5. These parameters must be measured using pulse techniques, $t_0 = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

	PARAMETER			MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.39	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

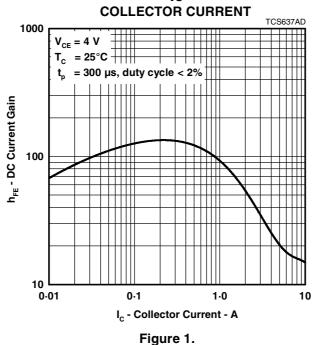
	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = 6 A	$I_{B(on)} = 0.6 A$	$I_{B(off)} = -0.6 A$		0.6		μs
t _{off}	Turn-off time	$V_{BE(off)} = -4 V$	$R_L = 5 \Omega$	t_p = 20 μs , $dc \le 2\%$		1		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs



MAXIMUM SAFE OPERATING REGIONS

MAXIMUM FORWARD-BIAS SAFE OPERATING AREA

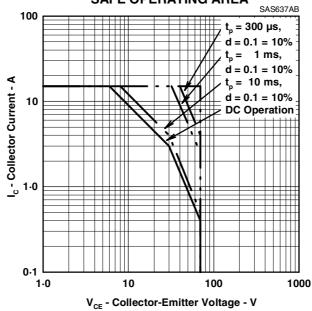


Figure 2.

THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

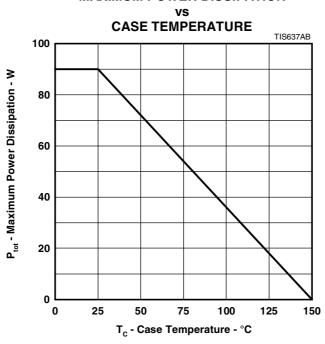


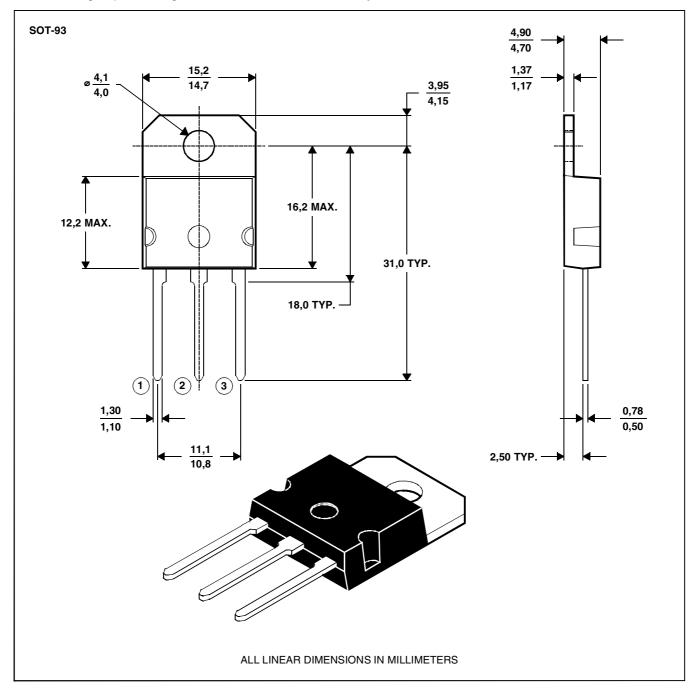
Figure 3.

MECHANICAL DATA

SOT-93

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

MDXXAW